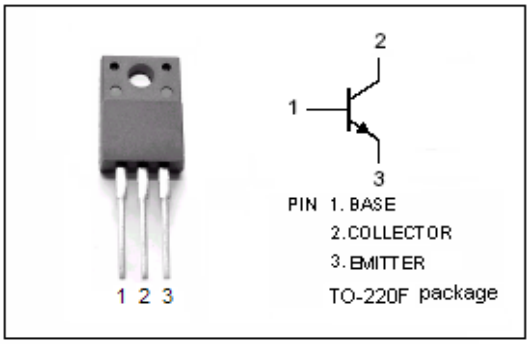
isc Silicon NPN Power Transistor 2SC2653H

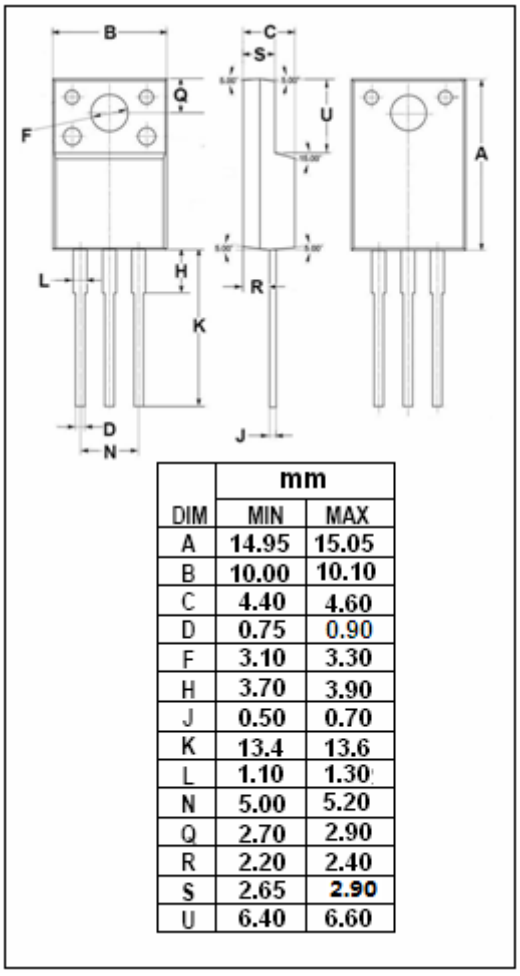


DESCRIPTION

- High V_{CEO}
- Large Pc

APPLICATIONS

- Color TV Horizontal
- Deflection Driver



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	480	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current-Continuous	0.2	A
Pc	Total Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-Emitter Sustaining Voltage	I_C=5mA ; I_B= 0; T_a=100℃	300			V
V_{CBO}	Collector-Base Sustaining Voltage	I_C=0.1mA ; I_E= 0; T_a=100℃	480			V
V_{EBO}	Emitter-Base Breakdown Voltage	I_E= 0.1mA; I_C= 0	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=50mA; I_B= 5mA			1	V
I_{CBO}	Collector Cutoff Current	V_{CB}=200V ; I_E= 0			2	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			2	μ A
h_{FE}	DC Current Gain	I_C= 10mA ; V_{CE}=10V	40		250	
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}=50V;f= 1.0MHz			4.5	pF
f_T	Current-Gain—Bandwidth Product	I_E=-10mA ; V_{CE}=30V	50			MHz